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NTE471
Silicon NPN Transistor
RF Power Output
P_O = 100W @ 30MHz

Description:

The NTE471 is a 28V epitaxial silicon NPN planar transistor designed primarily for SSB communications. This device utilizes state-of-the-art diffused emitter ballasting for improved ruggedness and reliability.

Features:

- Better than 15dB Gain at 30MHz and 100W (CW/PEP)
- Diffused Emitter Ballasting
- Withstands Infinite Mismatch at Operating Conditions
- Low Inductance Stripline Package
- Frequency = 30MHz
- Power Out = 100 Watts
- Voltage = 28 Volts
- Power Gain = 15dB

Absolute Maximum Ratings: (T_C = +25°C unless otherwise specified)

Collector–Base Voltage, V _{CBO}	65V
Collector–Emitter Voltage, V _{CEO}	36V
Emitter–Base Voltage, V _{EBO}4V
Maximum Collector Current, I _C	20A
Total Device Dissipation (T _C = +25°C), P _{tot}	270W
Maximum Junction Temperatures, T _J	+200°C
Storage Temperature Range, T _{stg}	–65° to +150°C
Thermal Resistance, Junction–to–Case, R _{thJC}	65°C/W

Electrical Characteristics: ($T_C = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CES}	$V_{CE} = 30\text{V}$, $V_{BE} = 0$	—	—	15	mA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 100\text{mA}$, $I_B = 0$, Note 1	36	—	—	V
	$V_{(BR)CES}$	$I_C = 100\text{mA}$, $V_{BE} = 0$, Note 1	65	—	—	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 10\text{mA}$, $I_C = 0$	4	—	—	V
DC Current Gain	h_{FE}	$V_{CE} = 5\text{V}$, $I_C = 5\text{A}$	10	50	—	
Dynamic Characteristics						
Power Output	P_O	$V_{CE} = 28\text{V}$, $f = 30\text{MHz}$	100	—	—	W
Power Gain	P_g	$V_{CE} = 28\text{V}$, $f = 30\text{MHz}$	15.6	16.0	—	dB
Capacitance	C_{ob}	$V_{EB} = 30\text{V}$, $I_E = 0$, $f = 1\text{MHz}$	—	250	—	pF

Note 1. Pulsed through a 25mH inductor.

